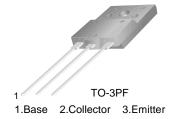


TIP145F/146F/147F

Monolithic Construction With Built In Base-Emitter Shunt Resistors

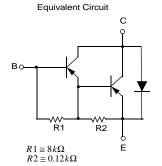
- High DC Current Gain : $h_{FE} = 1000 @ V_{CE} = -4V$, $I_{C} = -5A$ (Min.)
- Industrial Use
- Complement to TIP140F/141F/142F



PNP Epitaxial Darlington Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

| Symbol | Parameter | Value | Units | |
|------------------|--|------------|-------|--|
| V _{CBO} | Collector-Emitter Voltage: TIP145F | - 60 | V | |
| | : TIP146F | - 80 | V | |
| | : TIP147F | - 100 | V | |
| V _{CEO} | Collector-Emitter Voltage: TIP145F | - 60 | V | |
| | : TIP146F | - 80 | V | |
| | : TIP147F | - 100 | V | |
| V _{EBO} | Emitter-Base Voltage | - 5 | V | |
| I _C | Collector Current (DC) | - 10 | Α | |
| I _{CP} | Collector Current (Pulse) | - 15 | Α | |
| I _B | Base Current (DC) | - 0.5 | Α | |
| P _C | Collector Dissipation (T _C =25°C) | 60 | W | |
| TJ | Junction Temperature | 150 | °C | |
| T _{STG} | Storage Temperature | - 65 ~ 150 | °C | |



Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|------------------------|---|---|-------|------|-------|-------|
| V _{CEO} (sus) | Collector-Emitter Sustaining Voltage : TIP145F | I _C = - 30mA, I _B = 0 | - 60 | | | V |
| | : TIP146F | , , , | - 80 | | | V |
| | : TIP147F | | - 100 | | | V |
| I _{CEO} | Collector Cut-off Current | | | | | |
| | : TIP145F | $V_{CE} = -30V, I_{B} = 0$ | | | - 2 | mA |
| | : TIP146F | $V_{CE} = -40V, I_{B} = 0$ | | | - 2 | mA |
| | : TIP147F | $V_{CE} = -50V, I_{B} = 0$ | | | - 2 | mA |
| I _{CBO} | Collector Cut-off Current | | | | | |
| | : TIP145F | $V_{CB} = -60V, I_{E} = 0$ | | | - 1 | mA |
| | : TIP146F | $V_{CB} = -80V, I_{E} = 0$ | | | - 1 | mA |
| | : TIP147F | $V_{CB} = -100V, I_{E} = 0$ | | | - 1 | mA |
| I _{EBO} | Emitter Cut-off Current | $V_{BE} = -5V, I_{C} = 0$ | | | - 2 | mA |
| h _{FE} | DC Current Gain | $V_{CE} = -4V, I_{C} = -5A$ | 1000 | | | |
| | | $V_{CE} = -4V, I_{C} = -10A$ | 500 | | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | $I_C = -5A, I_B = -10mA$ | | | - 2 | V |
| | | $I_C = -10A, I_B = -40mA$ | | | - 3 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I _C = - 10A, I _B = - 40mA | | | - 3.5 | V |
| V _{BE} (on) | Base-Emitter ON Voltage | V _{CE} = - 4V, I _C = - 10A | | | - 3 | V |
| t _D | Delay Time | $V_{CC} = -30V, I_{C} = -5A$ | | 0.15 | | μs |
| t _R | Rise Time | $I_{B1} = -20 \text{mA}, I_{B2} = 20 \text{mA}$ | | 0.55 | | μs |
| t _{STG} | Storage Time | $R_L = 6\Omega$ | | 2.5 | | μs |
| t _f | Fall Time | 7 | | 2.5 | | μs |

Typical Characteristics

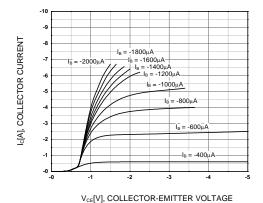


Figure 1. Static Characteristic

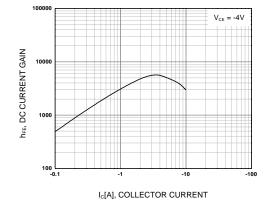


Figure 2. DC current Gain

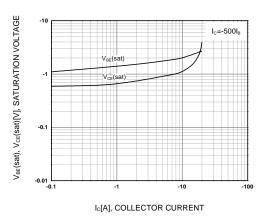


Figure 3. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

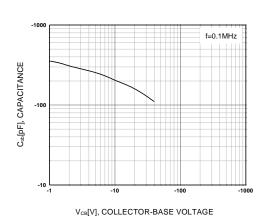


Figure 4. Collector Output Capacitance

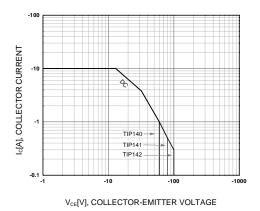


Figure 5. Safe Operating Area

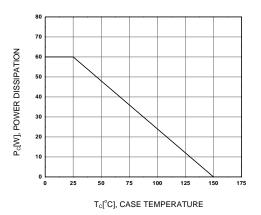
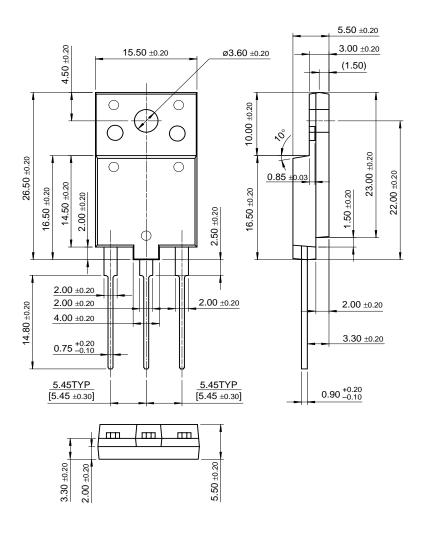


Figure 6. Power Derating

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Package Demensions

TO-3PF



Dimensions in Millimeters

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